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NPN-SWITCHING SILICON TRANSISTOR

Qualified per MIL-PRF-19500/251

DEVICES

2N2218	2N2219
2N2218A	2N2219A
2N2218AL	2N2219AL

LEVELS
JAN
JANTX
JANTXV
JANS *

* Also available in Radiation Hardened versions. See datasheet for JANSR2N2218 & JANSR2N2219

ABSOLUTE MAXIMUM RATINGS ($T_c = +25^{\circ}C$ unless otherwise noted)

Parameters / Test Conditions	Symbol	2N2218 2N2219	2N221A; L 2N2219A; L	Unit
Collector-Emitter Voltage	V _{CEO}	30	50	Vdc
Collector-Base Voltage	V _{CBO}	60	75	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	6.0	Vdc
Collector Current	I _C	800		mA
Total Power Dissipation (a) T _A = +25°C (a) T _C = +25°C	P _T		0.8 3.0	W W
Operating & Storage Junction Temp. Range	T _{op} , T _{stg}	-55	to +200	°C

TO-39 (TO-205AD) 2N2218, 2N2218A

2N2219, 2N2219A

THERMAL CHARACTERISTICS

Parameters / Test Conditions	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	59	°C/W

Note: (1) Derate linearly 4.6 mW/°C above $T_A > +25^{\circ}\text{C}$ (2) Derate linearly 17.0 mW/°C above $T_C > +25^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = +25^{\circ}C$, unless otherwise noted)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
OFF CHARACTERTICS					
Collector-Emitter Breakdown V $I_E = 10$ mAdc	oltage 2N2218; 2N2219 2N2218A; 2N2219A / AL	V _{(BR)CEO}	30 50		Vdc
Emitter-Base Cutoff Current $V_{EB} = 5.0$ Vdc $V_{EB} = 6.0$ Vdc $V_{EB} = 4.0$ Vdc	2N2218; 2N2219 2N2218A; 2N2219A / AL All Types	I _{EBO}		10 10 10	μAdc ηAdc
Collector-Base Cutoff Current $V_{CE} = 30Vdc$ $V_{CE} = 50Vdc$	2N2218; 2N2219 2N2218A; 2N2219A / AL	I _{CES}		10 10	ηAdc



TO-5 2N2218AL 2N2219AL



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ELECTRICAL CHARACTERISTICS ($T_A = +25^{\circ}C$, unless otherwise noted) (Con't)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Collector-Base Cutoff Current $V_{CB} = 50Vdc$ $V_{CB} = 60Vdc$ $V_{CB} = 60Vdc$ $V_{CB} = 75Vdc$	2N2218; 2N2219 2N2218; 2N2219 2N2218A; 2N2219A / AL 2N2218A; 2N2219A / AL	I _{CBO}		10 10 10 10	ηAdc μAdc ηAdc μAdc
ON CHARACTERTICS (3)					
Forward-Current Transfer Ratio $I_C = 0.1 \text{mAdc}, V_{CE} = 10 \text{Vdc}$ $I_C = 1.0 \text{mAdc}, V_{CE} = 10 \text{Vdc}$ $I_C = 10 \text{mAdc}, V_{CE} = 10 \text{Vdc}$	2N2218 2N2219 2N2218A; 2N2218AL 2N2219A; 2N2219AL 2N2218 2N2219 2N2218A; 2N2218AL 2N2219A; 2N2218AL 2N2219A; 2N2219AL 2N2218 2N2219 2N2218A; 2N2218AL 2N2219A; 2N2218AL	h _{FE}	20 35 30 50 25 50 35 75 35 75 40 100	150 325 150 325	
$I_{C} = 150 \text{mAdc}, V_{CE} = 10 \text{Vdc}$ $I_{C} = 500 \text{mAdc}, V_{CE} = 10 \text{Vdc}$	2N2219A, 2N2219AL 2N2218; A; AL 2N2219; A; AL 2N2218; A; AL 2N2219; A; AL		40 100 20 30	120 300	
Collector-Emitter Saturation Voltage					
$I_C = 150$ mAdc, $I_B = 15$ mAdc $I_C = 500$ mAdc, $I_B = 50$ mAdc	2N2218; 2N2219 2N2218A; 2N2219A / AL 2N2218; 2N2219 2N2218A; 2N2219A / AL	V _{CE(sat)}		0.4 0.3 1.6 1.0	Vdc
Base-Emitter Saturation Voltage $I_C = 150$ mAdc, $I_B = 15$ mAdc	2N2218; 2N2219 2N2218A; 2N2219A / AL	V _{BE(sat)}	0.6 0.6	1.3 1.2	Vdc
$I_{\rm C} = 500$ mAdc, $I_{\rm B} = 50$ mAdc	2N2218; 2N2219 2N2218A; 2N2219A / AL	• BE(sat)		2.6 2.0	vue



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DYNAMIC CHARACTERISTICS

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Magnitude of Small-Signal Forward Curren $I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, $f = 100$ MHz	t Transfer Ratio	h _{fe}	2.5	12	
Small-Signal Forward Current Transfer Rat $I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ kHz	io 2N2218 2N2219 2N2218A, AL 2N2219A, AL	h _{fe}	25 50 35 75		
Output Capacitance $V_{CB} = 10$ Vdc, $I_E = 0$, 100 kHz $\leq f \leq 1.0$ MHz	z	C_{obo}		8.0	pF
Input Capacitance $V_{EB} = 0.5$ Vdc, $I_C = 0$, 100 kHz $\leq f \leq 1.0$ MH	Z	C _{ibo}		25	pF

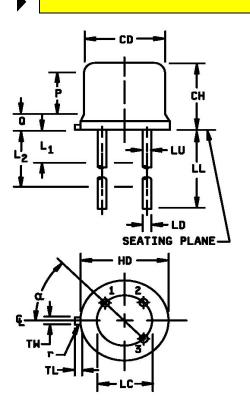
SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit	
$V_{CC} = 30Vdc; I_C = 150mAdc; I_{B1} = 15mAdc$					
Turn-On Time	21/22/10 21/22/10			10	
(See Figure 3 of MIL-PRF-19500/251)	2N2218, 2N2219 2N2218A, 2N2219A / AL	t _{on}		40 35	ηs
Turn-Off Time (See Figure 4 of MIL-PRF-19500/251)	2N2218, 2N2219 2N2218A, 2N2219A / AL	$t_{\rm off}$		250 300	ηs

(3) Pulse Test: Pulse Width = $300\mu s$, Duty Cycle $\leq 2.0\%$.



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	Dimensions				
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
СН	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08	3 TP	7
LD	.016	.019	0.41	0.48	8, 9
LL		See no	ote 14		
LU	.016	.019	0.41	0.48	8, 9
L ₁		.050		1.27	8, 9
L ₂	.250		6.35		8, 9
Р	.100		2.54		7
Q		.030		0.76	5
TL	.029	.045	0.74	1.14	3, 4
TW	.028	.034	0.71	0.86	3
r		.010		0.25	10
α	45°	ТР	45°	7	

PACKAGE DIMENSIONS

NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- 6. CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- 7. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- 8. Dimension LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
- 9. All three leads.
- 10. The collector shall be internally connected to the case.
- 11. Dimension r (radius) applies to both inside corners of tab.
- 12. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
- 13. Lead 1 =emitter, lead 2 =base, lead 3 =collector.
- 14. For L suffix devices (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max. For non-L suffix types (TO-39), dimension LL = .5 inch (12.70 mm) min. and .750 inch (19.05 mm) max.

FIGURE 1. Physical dimensions (similar to TO-39, TO-5).

T4-LDS-0091 Rev. 2 (101484)

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